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(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, F-38190 Bernin (FR).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **NEYRET, Eric** [FR/FR]; 2, rue Lesdiguières, F-38360 Sassenage (FR). **MALEVILLE, Christophe** [FR/FR]; 90, rue du Château, F-38660 La Terrasse (FR). **ESCARNOT, Ludovic** [FR/FR]; 11, rue de la Libération, F-38610 Gieres (FR).

(74) Agent: **MARTIN, Jean-Jacques**; Cabinet Regimbeau, 20, rue de Chazelles, F-75847 Paris Cedex 17 (FR).

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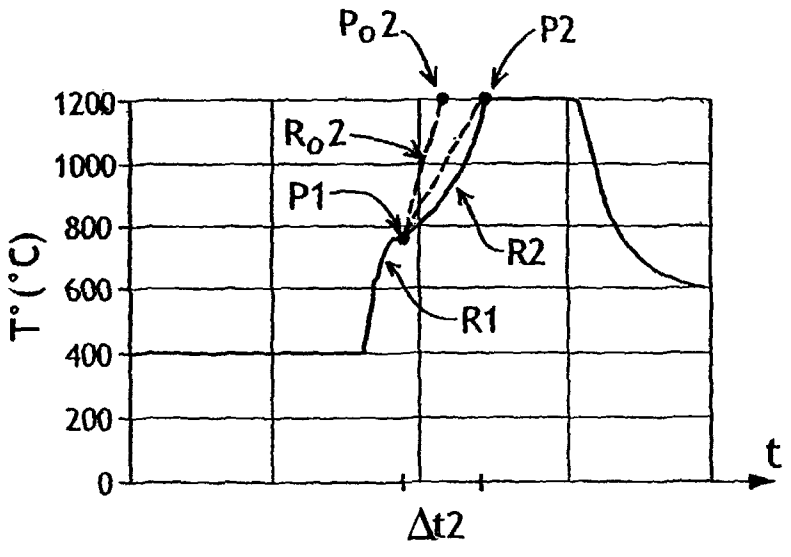
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(54) Title: RAPID ANNEALING PROCESS FOR WAFERS IN SEMICONDUCTOR MATERIAL



(57) Abstract: The invention relates to a surface treatment process for a wafer of material chosen among the semiconductor materials, the wafer having been obtained via a transfer technique, and the process comprising a rapid annealing stage comprising successively; a) a first ramp of temperature rise intended to initiate heating, b) a first stabilization halt intended to stabilize the temperature, c) a second ramp of temperature rise, characterized in that during the second ramp, the average slope of temperature rise has a first value within a first range of temperatures known as low, and then increases within a range of temperatures known as high.

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